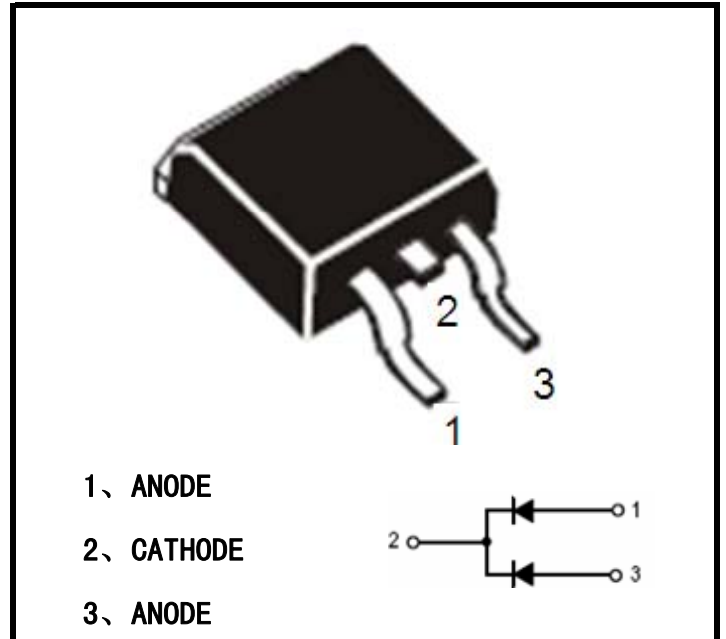


FEATURES

- *Schottky Barrier Chip
- *Guard Ring Die Construction for Transient Protection
- *Low Power Loss, High Efficiency
- *High Surge Capability
- *High Current Capability and Low Forward Voltage Drop
- *For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications

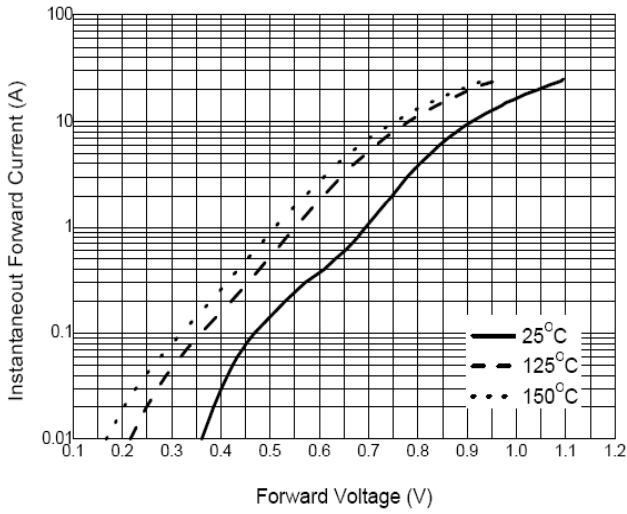
PACKAGE



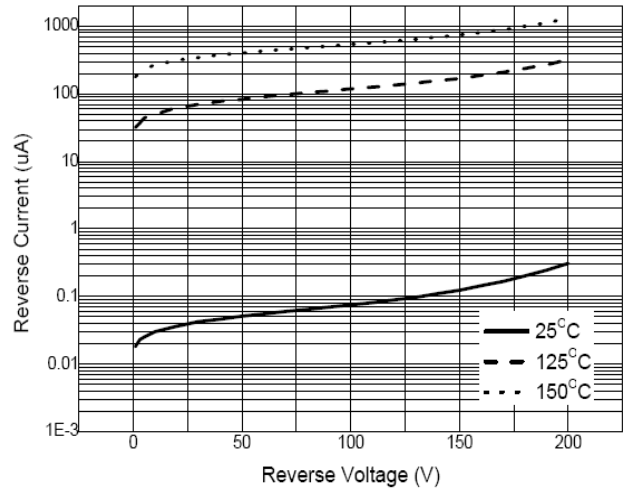
ELECTRICAL CHARACTERISTICS (T_{amb}=25°C)

Characteristic	Symbol	MBR10200CT	Unit
Peak Repetitive Reverse Voltage	V _{RRM}	200	V
Working Peak Reverse Voltage	V _{RWM}		
DC Blocking Voltage	V _R		
Average Rectified Output Current	I _{F(per leg)}	5	A
	I _{F(Total)}	10	
Non-Repetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60Hz)	I _{FSM}	150	A
Maximum Instantaneous Forward Voltage @IF=5A, TC=25°C @IF=5A, TC=125°C	V _F	0.92	V
		0.82	
Peak Reverse Current @Tc=25 °C at Rated DC Blocking Voltage @Tc=125°C	I _R	0.1	mA
		5	
Operating and Storage Temperature Range	T _J , T _{STG}	-65 to +150	°C
Maximum Thermal Resistance	θ _{JC}	3	°C/W
	θ _{JA}	60	

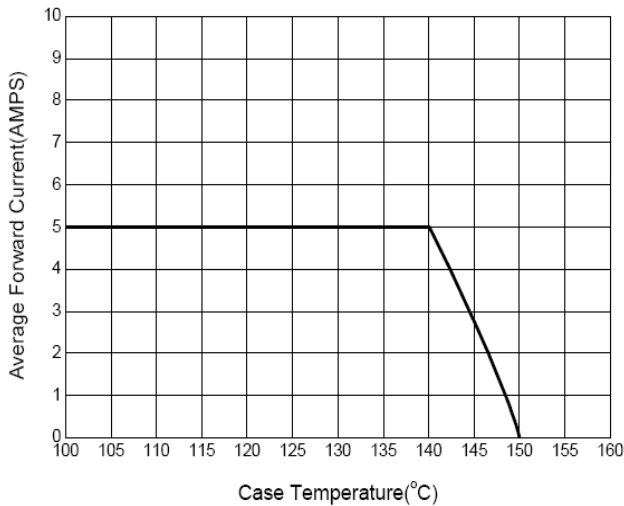
■ Transistor encapsulation figure



Typical Forward Voltage Per Diode

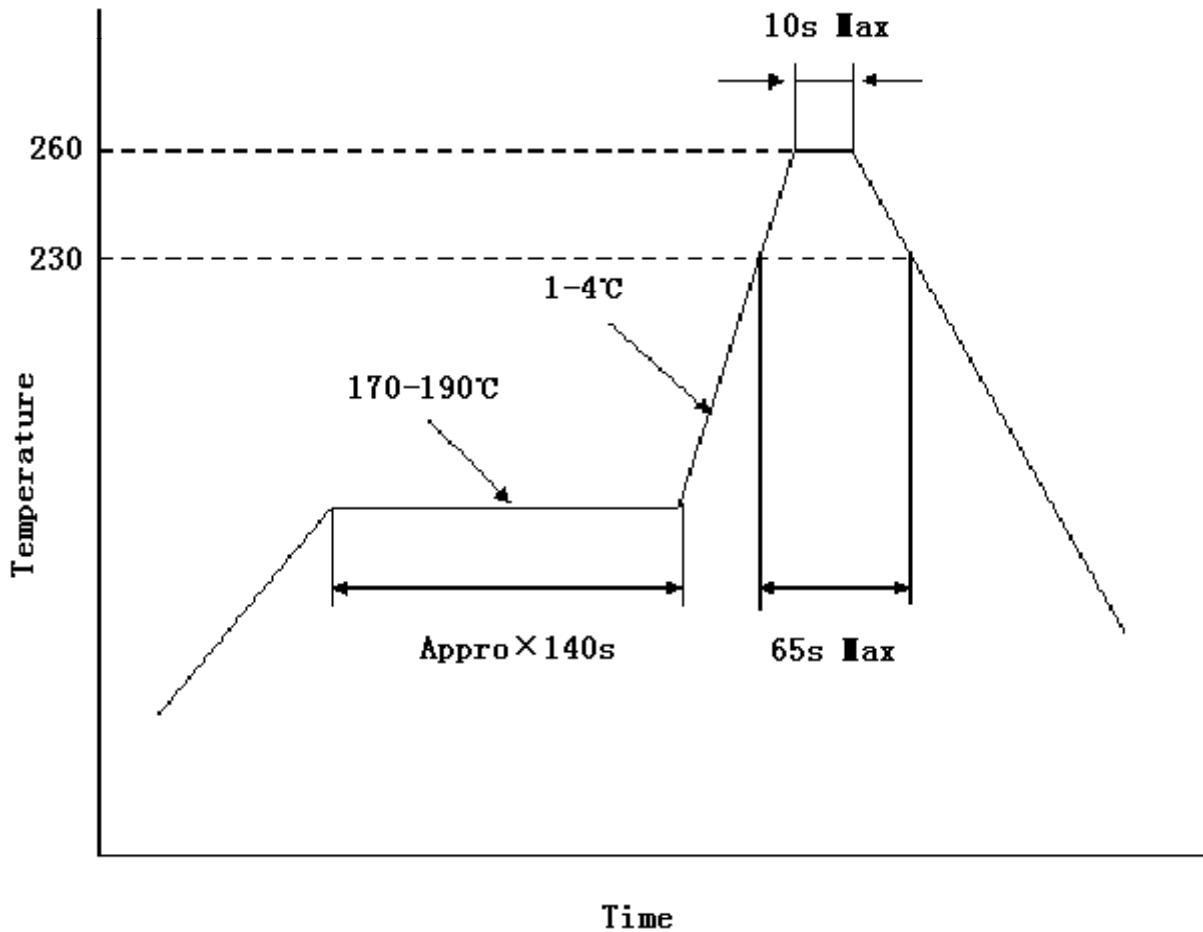


Typical Reverse Current Per Diode



Average Forward Forward Current vs.
Case Temperature Per Diode

■ Reflow Soldering Temperature Profile



TO-263 MECHANICAL DATA

UNIT: mm

SYMBOL	MIN	NOM	MAX	SYMBOL	MIN	NOM	MAX
A	4.42		4.72	E	8.99		9.29
B	1.22		1.32	e1	2.44		2.64
b	0.76		0.86	e2	4.98		5.18
b1	1.22		1.32	L1	15.19		15.79
b2	0.33		0.43	L2	1.94		2.19
C	1.22		1.32	L3			
D	9.95		10.25				

